

isc N-Channel MOSFET Transistor
R6507ENX
FEATURES

- Drain Current $-I_D = 7A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 650V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 665m\ \Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

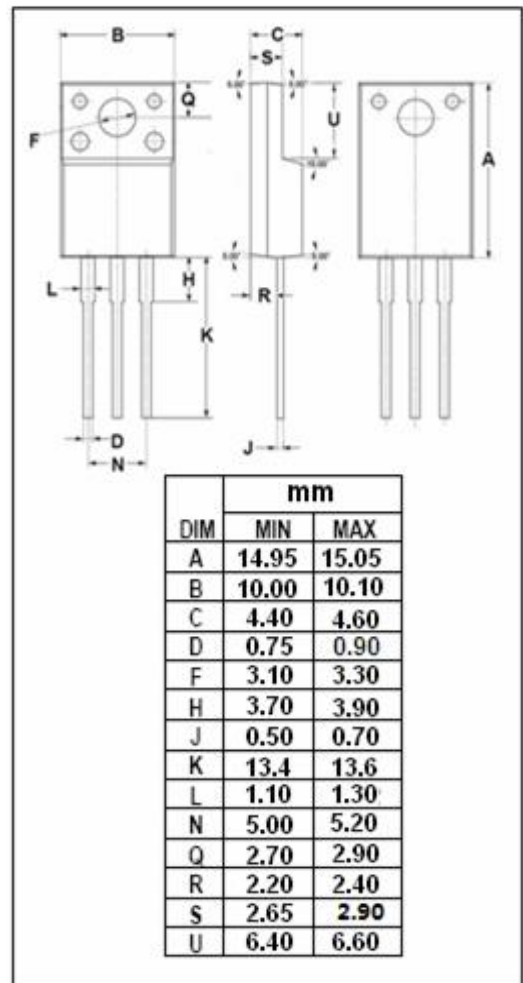
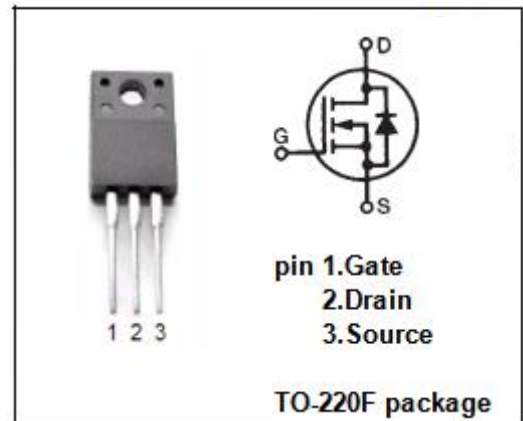
- Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	7	A
I_{DM}	Drain Current-Single Pluse	21	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	46	W
T_J	Max. Operating Junction Temperature	-55~150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.7	$^\circ C/W$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	650		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =200uA	2	4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =2.4A		665	mΩ
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650V; V _{GS} = 0 V _{DS} = 650V; V _{GS} = 0@T _J =125°C		100 1000	μA
V _{SD}	Forward On-Voltage	I _S = 7A; V _{GS} = 0		1.5	V

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